



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP075/NVLS-000820 Applicant: Tipton et al. Filing Date September 26, 2003	Application No.: 10/672,311 Group 2823
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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1A	6,340,628	01/22/02	Van Cleemput, et al.			
	2A	6,383,955	05/07/02	Matsuki, et al.			
	3A	6,596,654	07/22/03	Bayman, et al.			
	4A	4,885,262	12/5/89	Ting et al.			
	5A	5,686,054	11/11/97	Barthel et al.			
	6A	5,851,715	12/22/98	Barthel et al.			
	7A	6,140,252	10/31/00	Cho et al.			
	8A	6,392,017	5/21/02	Chandrashekar			
	9A	6,386,466	5/14/02	Ozawa et al.			
	10A	4,357,451	11/2/82	McDaniel			
	11A	6,479,374	11/12/02	Ioka et al.			
	12A	6,548,113	4/15/03	Birnbaum et al.			
	13A	6,329,017	12/11/01	Lu et al.			
	14A	2004/0099952	05/27/04	Goodner et al.			
	15A	2004/0102031	05/27/04	Kloster et al.			
	16A	2004/0185679	09/23/04	Ott et al.			

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	17A	Jan, C.H., et al, <i>90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology</i> , 2003 IEEE Interconnect Technology Conference.
	18A	Wu et al., U.S. Application No. 10/789,103 (Atty Docket No.: NOVLP094), entitled: Methods For Producing Low-K Cdo Films With Low Residual Stress
	19A	Wu et al., U.S. Application No. 10/820,525 (Atty Docket No.: NOVLP091), entitled: Methods For Producing Low-K Cdo Films With Low Residual Stress
	20A	Wu et al., U.S. Application No. 10/800,409 (Atty Docket No.: NOVLP098), entitled: Methods For Producing Low-K CDO Films
Examiner	Date Considered <i>7/11/2005</i>	

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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1B	6,848,458	02/01/05	Shrinivasan et al.			02/05/02
	2B	6,805,801	10/19/04	Humayun et al.			03/13/02
	3B	6,391,932	05/21/02	Gore et al.			08/08/00
	4B	5,789,027	08/04/98	Watkins et al.			11/12/96
	5B	5,700,844	12/23/97	Hedrick et al.			04/09/96
	6B	20030157248	08/21/03	Watkins et al.			11/21/02
	7B	20020123240	09/05/02	Gallagher et al.			11/30/01
	8B	20040096672	05/20/04	Lukas et al.			11/14/02

Other Documents

	9B	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030)
	10B	U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028)
	11B	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1)
	12B	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064)
	13B	Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Atty Dkt: NOVLP069).
Examiner		Date Considered
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U.S. Patent Documents

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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1	WO95/07543	03.16.95	WIPO			X	
Examiner 				Date Considered	7/11/2005			

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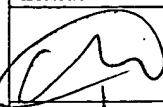

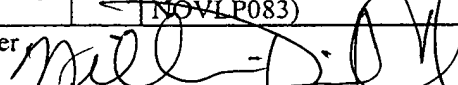
Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	Humayun et al., "Method for Forming Porous Films By Porogen Removal Combined With In Situ Surface Modification", Novellus Corporation, Application No. 10/404,693, filed 3/31/03, pages 1-32. Atty. Docket No. NOVL064/NVLS-0007
	C2	Tipton et al., "Method for Removal of Porogens From Porous Low-K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVL069/NVLS-000821
	C3	Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/800,377, filed 3/11/04, pages 1-31. Atty. Docket No. NOVL089/NVLS-2887
	C4	Wu et al., "Method and Apparatus of UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/807,680, filed 3/23/04, pages 1-34. Atty. Docket No. NOVL097/NVLS-2906
	C5	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure", U.S. Patent Application No. 10/825,888, filed April 16, 2004 (Atty Dkt: NOVL088US/NVLS-2882)
	C6	R.D. Miller et al., "Phase-Separated Inorganic-Organic Hybrids for Microelectronic Applications," MRS Bulletin, October 1997, Pages 44-48
	C7	Jin et al., "Nanoporous Silica as an Ultralow-k Dielectric," MRS Bulletin, October 1997, Pages 39-42
	C8	Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodicity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572
	C9	Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured Al," Journal of the Electrochemical Society, 148 (4) B152-B156 (2001) Pages B152-B156
	C10	Holland et al., "Nonlithographic Technique for the Production of Large Area High Density Gridded Field Sources," J. Vac. Sci. Technol. B 17(2), Mar/Apr. 1999, Pages 580-582
	C11	Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772
	C12	Clube et al., "White Paper from Holotronic Technologies SA; downloaded from www.hdotronic.com/whitepaper/fine-patt.pdf on March 12, 2002
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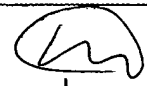

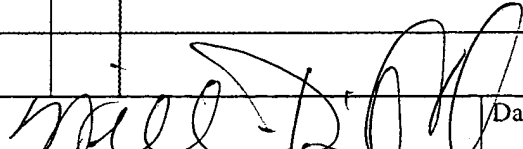
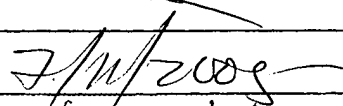
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C13	Meli et al., "Self-Assembled Masks for the Transfer of Nanometer-Scale Patterns into Surfaces: Characterization by AFM and LFM", Nano Letters, Vol. 2, No. 2, 2002, 131-135
	C14	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003.
	C15	Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), 56 (2003).
	C16	Van Bavel et al., Future Fab International, 16, (2004).
	C17	Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003.
	C18	Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International.
	C19	Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003.
	C20	Bhadri N. Varadarajan, "Tensile Silicon Nitride - P1264 NESL", C & F Study, August 21, 2003.
	C21	Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20, 2004, pages 1-24. [Atty Docket No. NOVLP108/NVLS-2933].
	C22	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt: NOVLP099)
	C23	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Office Action dated March 2, 2005, (Atty Dkt: NOVLP099)
	C24	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Final Office Action dated June 13, 2005, (Atty Dkt: NOVLP099)
	C25	Wang et al., "Plasma Detemplating And Silanol Capping Of Porous Dielectric Films", U.S. Application No. 10/785,235, filed February 23, 2004 (Atty Dkt: NOVLP085)
	C26	Varadarajan et al., "Tensile Dielectric Films Using UV Curing", U.S. Application No. 10/972,084, filed October 22, 2004 (Atty Dkt: NOVLP122)
	C27	Fox et al., "Method For Improving Mechanical Properties Of Low Dielectric Constant Materials", U.S. Application No. 10/849,568, filed May 18, 2004 (Atty Dkt: NOVLP083)
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 	C28	Fox et al., "Methods For Producing Low-Stress Carbon-Doped Oxide Films With Improved Integration Properties", U.S. Application No. 10/987,208, filed November 12, 2004 (Atty Dkt: NOVLP104)
	C29	Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt: NOVLP100)
	C30	Draeger et al., "Creation Of Porosity In Low-K Films By Photo-Disassociation Of Imbedded Nanoparticles," U.S. Application No. 11/146,456, filed June 6, 2005 (Atty Dkt: NOVLP100X1)
	C31	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 10/927,777, filed August 27, 2004 (Atty Dkt: NOVLP106)
	C32	Wu et al., "Methods For Improving Integration Performance Of Low Stress CDO Films", U.S. Application No. 10/941,502, filed September 14, 2004 (Atty Dkt: NOVLP107)
	C33	Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low-K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115)
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